

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings of claims in the application:

**Listing of Claims:**

1. (Currently amended) A method for forming a storage node of a capacitor in a semiconductor device, the method comprising the steps of:  
forming a first amorphous silicon layer doped with ~~an impurity in a predetermined~~ a first doping concentration, the first doping concentration being of a dose suppressing to  
suppress dopants from locally agglomerating;  
forming ~~an impurity undoped~~ a second amorphous silicon layer that is  
substantially undoped on the first amorphous silicon layer in an in-situ condition;  
~~forming a storage node by patterning the first amorphous silicon layer and the~~  
second amorphous silicon layer to form a first storage node;  
converting the second amorphous silicon layer to form a plurality of forming  
silicon grains on a surface an inner wall of the first amorphous silicon layer of the storage node,  
wherein substantially all of the second amorphous silicon layer is converted to the silicon grains  
to expose portions of the inner wall of the first amorphous silicon layer; and  
doping ~~the impurity to the first~~ storage node and the silicon grains with dopants  
until reaching a second predetermined doping concentration is reached, the second doping  
concentration being of sufficient dosage to provide requisite for providing conductivity required  
by to the first storage node,  
wherein a dielectric layer is formed over the doped first storage node and a second  
storage node is formed over the dielectric layer.

2. (Currently amended) The method as recited in claim 1, wherein the first ~~impurity~~ doping concentration ranges from about  $1 \times 10^{19}/\text{cm}^3$  to about  $9 \times 10^{19}/\text{cm}^3$   ~~$2 \times 10^{20}/\text{cm}^3$~~  and the second ~~impurity~~ doping concentration ranges from about  $24 \times 10^{20}/\text{cm}^3$  to about  $1 \times 10^{22}/\text{cm}^3$ .

3. (Currently amended) The method as recited in claim 1, wherein the first doping concentration ranges from about  $1 \times 10^{19}/\text{cm}^3$  to about  $9 \times 10^{19}/\text{cm}^3$  and the second doping concentration ranges from about  $24 \times 10^{20}/\text{cm}^3$  to about  $1 \times 10^{22}/\text{cm}^3$ , wherein the step of doping the impurity onto the first storage node and the silicon grains ~~proceeds by~~ involves performing one doping method of a chamber plasma doping method in an atmosphere of a gas containing phosphorus.

4. (Original) The method as recited in claim 3, wherein the chamber plasma doping is performed at a temperature ranging from about 700 °C to about 800 °C and a pressure ranging from about 1.5 torr to about 2.5 torr for about 2 minutes and about 5 minutes by supplying a plasma power ranging from about 300 W to about 500 W and phosphine ( $\text{PH}_3$ ) flowed with a quantity of about 300 sccm to about 500 sccm.

5. (Withdrawn) The method as recited in claim 1, wherein the step of doping the impurity onto the storage node and the silicon grains proceeds by performing another doping method of a furnace annealing in an atmosphere of a gas containing phosphorus.

6. (Withdrawn) The method as recited in claim 5, wherein the furnace annealing is performed at a temperature in a range from about 600 °C to about 750 °C and a pressure ranging from about 5 torr to about 10 torr for about 1 hour to about 2 hours by flowing  $\text{PH}_3$  gas with a quantity ranging from about 100 sccm to about 200 sccm.

7. (Withdrawn) The method as recited in claim 1, wherein the step of doping the impurity onto the storage node and the silicon grains further includes the steps of:  
performing a chamber plasma doping in an atmosphere of a gas containing phosphorus; and  
diffusing the doped impurity through a furnace annealing.

8. (Withdrawn) The method as recited in claim 7, wherein the chamber plasma doping is performed at a temperature ranging from about 700 °C to about 800 °C and a pressure ranging from about 1.5 torr to about 2.5 torr for about 1 minute and about 5 minutes by

supplying a plasma power in a range from about 300 W to about 500 W and PH<sub>3</sub> gas flowed with a quantity ranging from about 100 sccm to about 500 sccm.

9. (Withdrawn) The method as recited in claim 7, wherein the furnace annealing is performed at a temperature ranging from about 600 °C to about 750 °C and a pressure ranging from about 5 torr to about 10 torr in an atmosphere of nitrogen for about 1 hour to about 2 hours.

10. (Currently amended) The method as recited in claim 1, wherein the ~~converting step of forming the silicon grains on the surface of the storage node~~ further includes the step of cleaning the surface of the first storage node on which the silicon grains are formed.

11. (Currently amended) The method as recited in claim 10, wherein the step of cleaning the surface of the first storage node proceeds by using a wet chemical such as hydrogen fluoride (HF) and buffered oxide etchant (BOE).

12. (Withdrawn) A method for fabricating a capacitor of a semiconductor device, comprising the steps of:

forming an insulation layer having contact holes on an upper surface of a substrate;

forming a plurality of plugs connected to the substrate by being filled into the contact holes;

forming an isolation layer having holes exposing the plurality of the plugs on the insulation layer;

forming a first amorphous silicon layer doped with an impurity in a predetermined first doping concentration suppressing dopants from locally agglomerating;

forming an impurity undoped second amorphous silicon layer on the first amorphous silicon layer in an in-situ condition;

forming a storage node by patterning the first amorphous silicon layer and the second amorphous silicon layer;

forming silicon grains on a surface of the storage node; and  
doping the impurity to the storage node and the silicon grains until reaching a second predetermined concentration for providing conductivity required by the storage node.

13. (Withdrawn) The method as recited in claim 12, after the step of doping the impurity onto the storage node and the silicon grains, further comprising the steps of:

removing selectively the isolation layer;  
doping additionally the impurity to compensate a doping profile of the storage node; and

forming sequentially a dielectric layer and a plate on the storage node.

14. (Withdrawn) The method as recited in claim 12, after the step of doping the impurity onto the storage node and the silicon grains, further comprising the step of forming sequentially a dielectric layer and a plate on the storage node and the isolation layer.

15. (Withdrawn) The method as recited in claim 13, wherein the step of doping additionally the impurity to compensate the doping profile of the storage node proceeds by performing one doping method of a chamber plasma doping in an atmosphere of a gas containing phosphorus.

16. (Withdrawn) The method as recited in claim 15, wherein the chamber plasma doping is performed at a temperature ranging from about 700 °C to about 800 °C and a pressure ranging from about 1.5 torr to about 2.5 torr for about 2 minutes to about 5 minutes by supplying a plasma power ranging from about 300 W to about 500 w and PH<sub>3</sub> gas with a flow quantity ranging from about 300 sccm to about 500 sccm.

17. (Withdrawn) The method as recited in claim 13, wherein the step of doping additionally the impurity to compensate the doping profile of the storage node proceeds by performing another doping method of a furnace annealing in an atmosphere of a gas containing phosphorus.

18. (Withdrawn) The method as recited in claim 17, wherein the furnace annealing is performed at a temperature ranging from about 600 °C to about 750 °C and a pressure ranging from about 5 torr to about 10 torr for about 1 hour to about 2 hours by flowing PH<sub>3</sub> gas with a quantity in a range from about 100 sccm to about 200 sccm.

19. (Withdrawn) The method as recited in claim 12, wherein the first doping concentration ranges from about  $1 \times 10^{19}/\text{cm}^3$  to about  $2 \times 10^{20}/\text{cm}^3$  and the second doping concentration ranges from about  $24 \times 10^{20}/\text{cm}^3$  to about  $1 \times 10^{22}/\text{cm}^3$ .

20. (Withdrawn) The method as recited in claim 12, wherein the step of doping the impurity on the storage node and the silicon grains proceeds by performing one method of a chamber plasma doping in an atmosphere of a gas containing phosphorus.

21. (Withdrawn) The method as recited in claim 20, wherein the chamber plasma doping is performed at a temperature ranging from about 700 °C to about 800 °C and a pressure ranging from about 1.5 torr to about 2.5 torr for about 2 minutes to about 5 minutes by supplying a plasma power in a range from about 300 W to about 500 W and PH<sub>3</sub> gas with a flow quantity ranging from about 300 sccm to about 500 sccm.

22. (Withdrawn) The method as recited in claim 12, wherein the step of doping the impurity on the storage node and the silicon grains proceeds by performing another method of a furnace annealing in an atmosphere of a gas containing phosphorus.

23. (Withdrawn) The method as recited in claim 22, wherein the furnace annealing is performed at a temperature ranging from about 600 °C to about 750 °C and a pressure ranging from about 5 torr to about 10 torr for about 1 hour to about 2 hours by flowing PH<sub>3</sub> gas with a quantity in a range from about 100 sccm to about 200 sccm.

24. (Withdrawn) The method as recited in claim 12, wherein the step of doping the impurity onto the storage node and the silicon grains includes the steps of:

performing a chamber plasma doping in an atmosphere of a gas containing phosphorus; and

diffusing the doped impurity through a furnace annealing.

25. (Withdrawn) The method as recited in claim 24, wherein the chamber plasma doping is performed at a temperature ranging from about 700 °C to about 800 °C and a pressure ranging from about 1.5 torr to about 2.5 torr for about 1 minute to about 5 minutes by supplying a plasma power in a range from about 300 W to about 500 W and PH<sub>3</sub> gas with a flow quantity ranging from about 300 sccm to about 500 sccm.

26. (Withdrawn) The method as recited in claim 24, wherein the furnace annealing is performed at a temperature ranging from about 600 °C to about 750 °C and a pressure ranging from about 5 torr to about 10 torr in an atmosphere of nitrogen for about 1 hour to about 2 hours.

27. (Withdrawn) The method as recited in claim 12, wherein the step of forming the silicon grains on the surface of the storage node further includes the step of cleaning the surface of the storage node on which the silicon grains are formed.

28. (Withdrawn) The method as recited in claim 27, wherein the step of cleaning the surface of the storage node proceeds by using a wet chemical such as HF or BOE.

29. (New) A method for forming a storage node of a capacitor in a semiconductor device, the method comprising:

providing a trench on a substrate;

forming a first amorphous silicon layer doped with a first doping concentration within the trench, the first amorphous silicon layer having inner and outer walls, the inner wall defining a space within the trench, the first doping concentration ranging from about  $1 \times 10^{19}/\text{cm}^3$  to about  $2 \times 10^{20}/\text{cm}^3$  to suppress dopants from locally agglomerating;

forming a second amorphous silicon layer that is substantially undoped on the first amorphous silicon layer in an in-situ condition;

patterning the first amorphous silicon layer and the second amorphous silicon layer to form a first storage node;

converting the second amorphous silicon layer to form a plurality of silicon grains on the inner wall of the first amorphous silicon layer, wherein substantially all of the second amorphous silicon layer is converted to the silicon grains to expose portions of the inner wall of the first amorphous silicon layer;

converting the first amorphous silicon layer to a polysilicon layer; and

doping the first storage node and the silicon grains with dopants until a second doping concentration is reached, the second doping concentration being of sufficient dosage to provide requisite conductivity to the first storage node,

wherein a dielectric layer is formed over the first storage node and a second storage node is formed over the dielectric layer and within the space defined in the trench.

30. (New) The method as recited in claim 29, the first doping concentration ranging from about  $1 \times 10^{19}/\text{cm}^3$  to about  $9 \times 10^{19}/\text{cm}^3$ .

31. (New) The method as recited in claim 30, wherein and the second doping concentration ranges from about  $24 \times 10^{20}/\text{cm}^3$  to about  $1 \times 10^{22}/\text{cm}^3$ .

32. (New) The method as recited in claim 30, wherein the doping step involves a chamber plasma doping in a phosphorus atmosphere.

33. (New) The method as recited in claim 30, wherein the chamber plasma doping is performed at a temperature ranging from about 700 °C to about 800 °C and a pressure ranging from about 1.5 torr to about 2.5 torr for about 2 minutes and about 5 minutes by supplying a plasma power ranging from about 300 W to about 500 W and phosphine ( $\text{PH}_3$ ) flowed with a quantity of about 300 sccm to about 500 sccm.

34. (New) The method as recited in claim 30, wherein the converting step further includes the step of cleaning the surface of the first storage node.

35. (New) The method as recited in claim 34, wherein the step of cleaning the surface of the first storage node involves using a wet chemical such as hydrogen fluoride (HF) and buffered oxide etchant (BOE).

36. (New) A method for forming a storage node of a capacitor in a semiconductor device, the method comprising:

providing a trench on a substrate;

forming a first amorphous silicon layer doped with a first doping concentration within the trench, the first amorphous silicon layer having inner and outer walls, the inner wall defining a space within the trench, the first doping concentration being of a dosage to suppress dopants from locally agglomerating;

forming a second amorphous silicon layer that is substantially undoped on the first amorphous silicon layer in an in-situ condition;

patterning the first amorphous silicon layer and the second amorphous silicon layer to form a first storage node;

converting the second amorphous silicon layer to form a plurality of silicon grains on the inner wall of the first amorphous silicon layer, wherein substantially all of the second amorphous silicon layer is converted to the silicon grains to expose portions of the inner wall of the first amorphous silicon layer;

converting the first amorphous silicon layer to a polysilicon layer; and

doping the first storage node and the silicon grains with dopants until a second doping concentration is reached, the second doping concentration being of sufficient dosage to provide requisite conductivity to the first storage node,

wherein a dielectric layer is formed over the first storage node and a second storage node is formed over the dielectric layer and within the space defined in the trench.